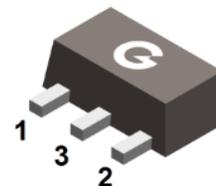
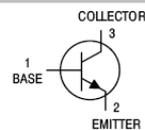


### Features

- Epitaxial planar die construction
- Switching and amplification in high voltage
- Low current
- High voltage
- Complementary to CXT5401
- RoHS compliant with Halogen-free

HF



SOT-89

### Mechanical Data

- Case: SOT-89
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
CXT5551	SOT-89	1000 pcs / Tape & Reel	1G6

### Maximum Ratings (@ T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	180	V
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Breakdown Voltage	V <sub>EB0</sub>	6	V
Collector Current (Continuous)	I <sub>C</sub>	0.6	A
Collector Current (Peak)	I <sub>CM</sub>	0.8	A

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation <sup>*1</sup>	P <sub>D</sub>	0.625	W
Thermal Resistance Junction-to-Air <sup>*1</sup>	R <sub>θJA</sub>	200	°C/W
Thermal Resistance Junction-to-Air <sup>*2</sup>	R <sub>θJA</sub>	60	°C/W
Thermal Resistance Junction-to-Case <sup>*2</sup>	R <sub>θJC</sub>	30	°C/W
Thermal Resistance Junction-to-Lead <sup>*2</sup>	R <sub>θJL</sub>	20	°C/W
Junction Temperature Range	T <sub>J</sub>	-65 ~ +150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 ~ +150	°C

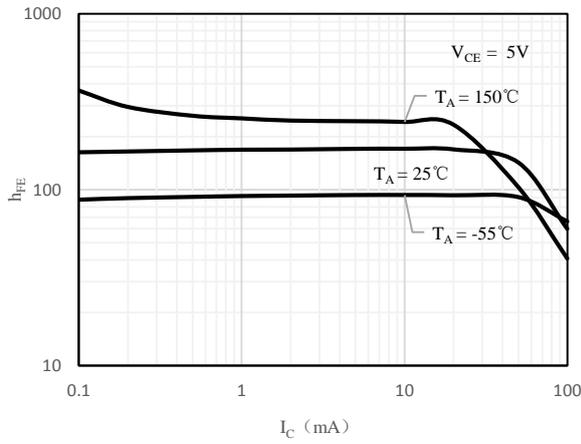
Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper

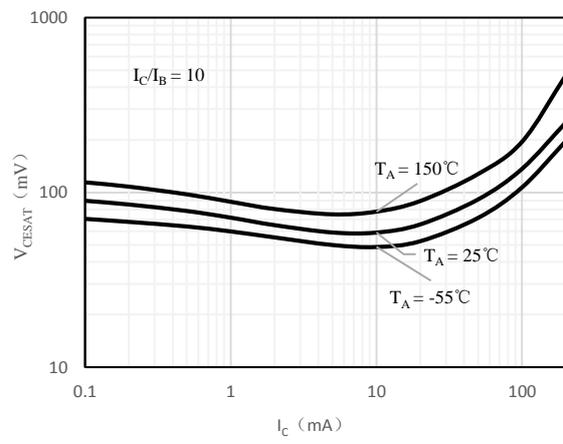
### Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	180	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}, I_B = 0$	160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 120\text{V}, I_E = 0$	-	-	50	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$	-	-	50	nA
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$	80	-	-	-
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	100	-	300	-
		$V_{CE} = 5\text{V}, I_C = 50\text{mA}$	30	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	-	0.15	V
		$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	0.2	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	-	1	V
		$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	1	V
Collector-base Output Capacitance	$C_{cbo}$	$V_{CB} = 10\text{V}, f = 1\text{MHz}, I_E = 0$	-	-	6	pF
Current-Gain— Bandwidth Product	$f_T$	$I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$	100	-	300	MHz
Noise Figure	NF	$I_C = 200\mu\text{A}, V_{CE} = 5\text{V}$ $F = 10\text{-}15.7\text{kHz}, R_S = 1.0\Omega$	-	-	8	dB

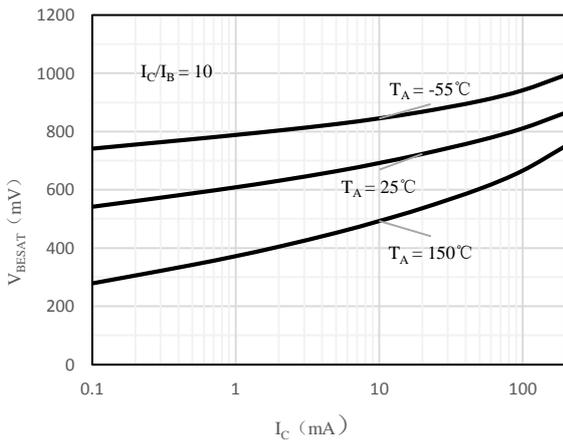
**Ratings and Characteristics Curves** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)



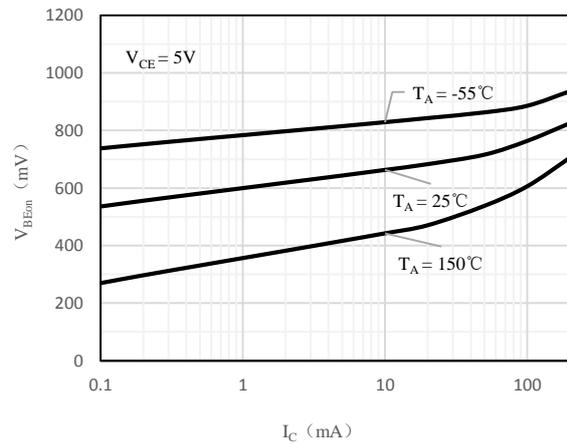
**Fig 1  $h_{FE}$  vs.  $I_C$**



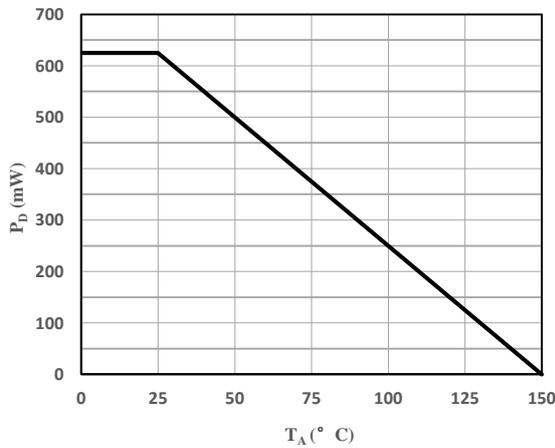
**Fig 2  $V_{CE(sat)}$  vs.  $I_C$**



**Fig 3  $V_{BE(sat)}$  vs.  $I_C$**

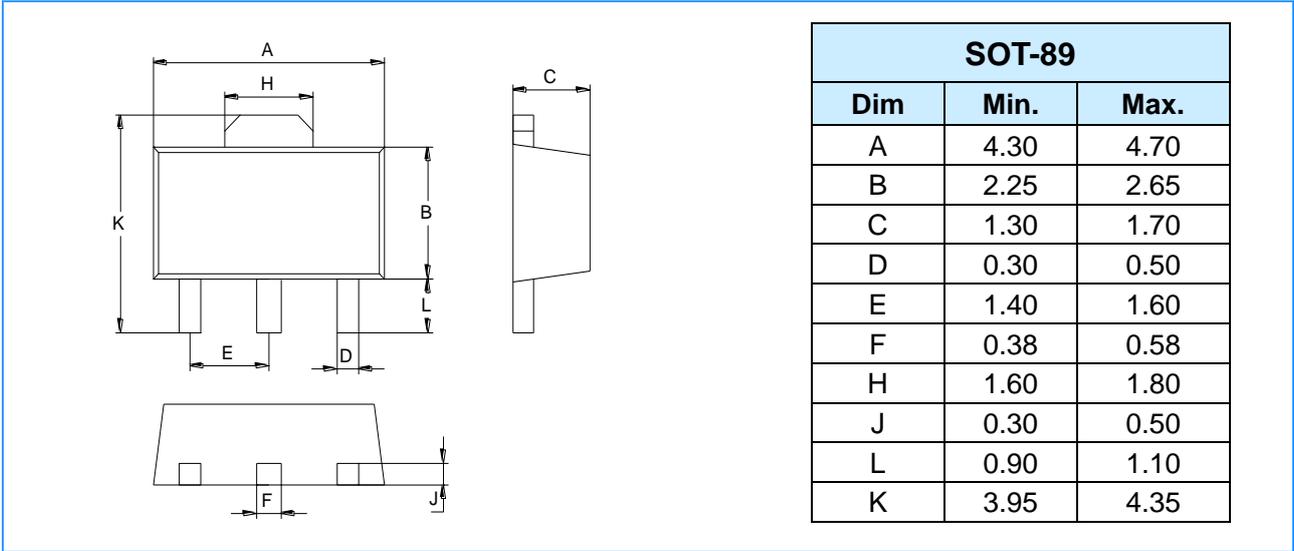


**Fig 4  $V_{BE(on)}$  vs.  $I_C$**



**Fig 5 Power Derating Curve**

**Package Outline Dimensions** (Unit: mm)



**Package Outline Dimensions** (Unit: mm)

